

“Influence of 4H-SiC substrate miscut on the epitaxy and microstructure of AlGaN/GaN heterostructures”. Gkanatsiou A, Lioutas CB, Frangis N, Polychroniadis EK, Prystawko P, Leszczynski M, Altantzis T, Van Tendeloo G, Materials science in semiconductor processing **91**, 159 (2019). <http://doi.org/10.1016/j.mssp.2018.11.008>